



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#9/13  
4/3/13  
Sunder

First Named Inventor: Matsudo

Group Art Unit: 2823

Application No.: 09/757,583

Examiner: Brairton, Scott A

Filing Date: 01/11/2001

For: METHOD FOR DEPOSITING TUNGSTEN SILICIDE FILM AND METHOD FOR  
PREPARING GATE ELECTRODE/WIRING

AMENDMENT AND RESPONSE TO OFFICE ACTION

Box Amendment  
Commissioner for Patents  
Washington, D.C. 20231

A response to the Office Action mailed October 23, 2002 is being timely filed  
with a two month extension of time. Applicants request amendment of the application as  
follows.

IN THE CLAIMS

Please add new claims 22-27 as follows.

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01 FC:1201 168.00 CH  
02 FC:1202 18.00 CH  
22. (New) A gate electrode/wiring structure comprising:

a polysilicon layer;  
a tungsten silicide layer formed on said polysilicon layer; and  
a silicon layer formed on said tungsten silicide layer,  
wherein the silicon layer has a thickness of 50 to 200 angstroms.

23. (New) A method for preparing a gate electrode/wiring as set forth in claim 8, wherein  
the silicon layer has a thickness of 50 to 200 angstroms.

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03 FC:1201 420.00 OP  
04 FC:1202 108.00 OP